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Vishay Semiconductors

Gen 2 High Performance Schottky Rectifier Not Insulated TO-244 Power Module 200 V, 400 A



PRIMARY CHARACTERISTICS				
I _{F(AV)} , module - T _C = 128 °C	400 A			
V_{R}	200 V			
Q _{rr} (typical)	540 nC			
t _{rr}	132 ns			
Туре	Modules - diode, Schottky			
Package	TO-244			
Circuit configuration	Two diodes common cathode			

FEATURES

- Max. T_J = 175 °C
- Trench MOS Barrier Schottky technology



- Ultra low forward voltage drop
- · Easy to use and parallel
- Optimized for power conversion: welding and industrial SMPS applications
- Designed for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

The VS-402CNQ20OPBF not insulated modules integrate two state of the art Trench MOS barrier Schottky technology rectifiers in the compact industry standard TO244 package.

These devices are thus intended for high frequency converters and switching power supplies.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_R		200	V	
		T _C = 25 °C	551		
Continuous forward current per diode	I _{F(DC)}	T _C = 85 °C	397	^	
		T _C = 143 °C	200	A	
Single pulse forward current per diode	I _{FSM}	T _C = 175 °C, t = 6 ms, square	2100		
Maximum power dissipation	P _D	T _C = 25 °C	789	W	
		T _C = 85 °C	474	T vv	
Operating junction temperatures	TJ		-40 to +175	°C	
Storage temperatures	T _{Stg}		-40 to +150	°C	

ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage	V_{BR}	I _R = 2mA	200	-	-	
	V _{FM}	I _F = 200 A	-	0.845	1.045	V
Forward voltage V _{FM}		I _F = 400 A	-	0.958	1.358	
		I _F = 200 A, T _J = 125 °C	-	0.715	-	
		I _F = 400 A, T _J = 125 °C	-	0.850	-	
Payaraa laakaga aurrant	I _{RM}	T _J = 25 °C, V _R = 200 V	-	50	200	μA
Reverse leakage current	I _{RM}	$T_J = 175 ^{\circ}\text{C}, V_R = 200 \text{V}$	-	198	500	mA
Maximum junction capacitance per leg	C _T	V _{DC} = 5 V, f = 1 MHz, 25 °C	-	-	20	nF
Series inductance	L _S	From top of terminal hole to mounting plane	-	5	-	nH



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS			TYP.	MAX.	UNITS
Dayaraa raaayan, tima	1	T _J = 25 °C	$I_F = 50 \text{ A},$ $dI_F/dt = 100 \text{ A/}\mu\text{s},$ $V_R = 100 \text{ V}$	-	132	-	ns
Reverse recovery time	t _{rr}	T _J = 125 °C		-	155	-	
Dools recovery average	rent I _{RRM}	T _J = 25 °C		=	6	-	^
Peak recovery current		T _J = 125 °C		-	8	-	A
D	0	T _J = 25 °C		-	540	-	0
neverse recovery charge	Reverse recovery charge Q _{rr}			-	840	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Thermal resistance,	per leg	Б	-	-	0.19		
junction to case	per module	R_{thJC}	-	-	0.095	°C/W	
Thermal resistance, case	to heatsink	R _{thCS}	R _{thCS} - 0.10 -				
Weight			-	68	-	g	
			-	2.4	-	oz.	
Mounting torque			30 (3.4) - 40 (4.6)				
Mounting torque center hole			12 (1.4)	-	18 (2.1)	lbf · in (N · m)	
Terminal torque			30 (3.4)	-	40 (4.6)	(14 - 111)	
Vertical pull			-	-	80	lbf ⋅ in	
2" lever pull			-	-	35	IDI • IDI	
Case style				TO-	-244		

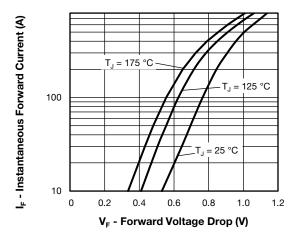


Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

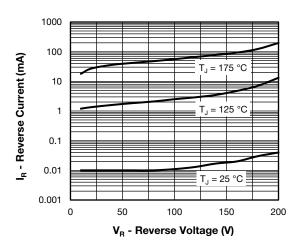


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)



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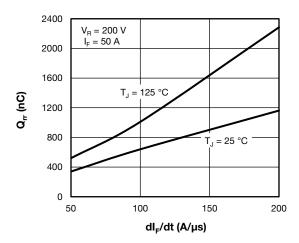


Fig. 3 - Typical Reverse Recovery Charge vs. dlFdt (Per Diode)

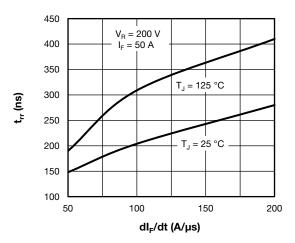


Fig. 4 - Typical Reverse Recovery Time vs dl_Fdt (Per Diode)

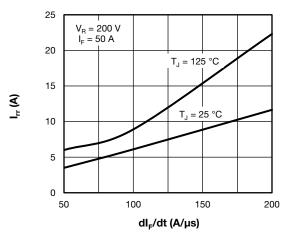


Fig. 5 - Typical Reverse Recovery Current vs. dl_Fdt (Per Diode)

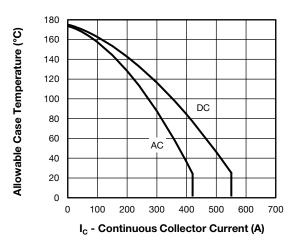


Fig. 6 - Maximum Continuous Forward Current vs.

Case Temperature

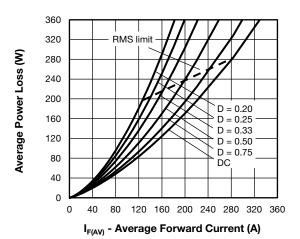


Fig. 7 - Average Power Loss vs Average Forward Current (Forward Power Loss Characteristics)

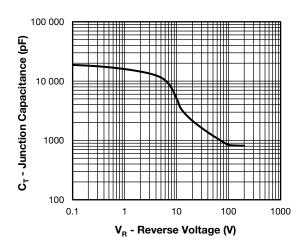


Fig. 8 - Typical Junction Capacitance vs. Reverse Voltage

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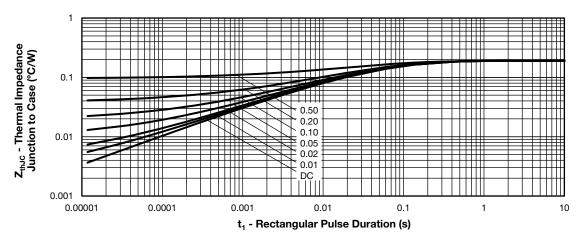
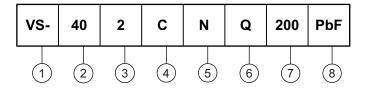


Fig. 9 - Z_{thJC} Maximum Thermal Impedance Junction to Case vs. t₁ Rectangular Pulse Duration

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Average current rating (x 10)

Product silicon identification

4 - Circuit configuration:

C = two diodes common cathode

5 - N = not isolated

6 - Q = Schottky rectifier diode

7 - 200 = 200 V

8 - PbF = lead (Pb)-free

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two diodes common cathode	С	Lug Lug terminal terminal anode 1 anode 2 Base common cathode			

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95021



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